Schottky Diode

### **DSA15IM200UC**

### preliminary

V <sub>RRM</sub>	=	200 V
I FAV	=	15 A
VF	=	0.78 V

High Performance Schottky Diode Low Loss and Soft Recovery Single Diode

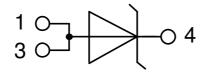
### Part number

### **DSA15IM200UC**

Marking on Product: SFMAUI



Backside: cathode



### Features / Advantages:

- Very low Vf
- Extremely low switching losses
- · Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

### **Applications:**

- · Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

### Package: TO-252 (DPak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

#### Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you. Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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# LIXYS

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Schottky					Ratings		
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V <sub>RSM</sub>	max. non-repetitive reverse blocki	ng voltage	$T_{VJ} = 25^{\circ}C$			200	V
V <sub>RRM</sub>	max. repetitive reverse blocking v	oltage	$T_{VJ} = 25^{\circ}C$			200	V
I <sub>R</sub>	reverse current, drain current	$V_{\text{R}}$ = 200 V	$T_{VJ} = 25^{\circ}C$			250	μA
		$V_{\text{R}}$ = 200 V	$T_{vJ} = 125^{\circ}C$			2.5	mA
VF	forward voltage drop	I <sub>F</sub> = 15 A	$T_{VJ} = 25^{\circ}C$			0.94	V
		$I_{F} = 30 \text{ A}$				1.10	V
		I <sub>F</sub> = 15 A	T <sub>vJ</sub> = 125°C			0.78	V
		$I_{F} = 30 \text{ A}$				0.95	V
I FAV	average forward current	T <sub>c</sub> = 150°C	T <sub>vJ</sub> = 175°C			15	Α
		rectangular d = 0.5					
V <sub>F0</sub>	threshold voltage		T <sub>vJ</sub> = 175°C			0.53	V
r <sub>F</sub>	slope resistance } for power lo	ess calculation only				10.8	mΩ
$\mathbf{R}_{thJC}$	thermal resistance junction to case	9				2	K/W
R <sub>thCH</sub>	thermal resistance case to heatsir	nk			0.50		K/W
P <sub>tot</sub>	total power dissipation		$T_c = 25^{\circ}C$			75	W
I <sub>FSM</sub>	max. forward surge current	t = 10 ms; (50 Hz), sine; $V_R = 0 V$	$T_{VJ} = 45^{\circ}C$			200	Α
C	junction capacitance	$V_{R}$ = 24 V f = 1 MHz	$T_{v_J} = 25^{\circ}C$		67		pF

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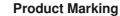


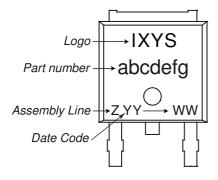
### DSA15IM200UC

preliminary

Package TO-252 (DPak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I <sub>RMS</sub>	RMS current	per terminal "			20	Α
T <sub>vj</sub>	virtual junction temperature		-55		175	°C
T <sub>op</sub>	operation temperature		-55		150	°C
T <sub>stg</sub>	storage temperature		-55		150	°C
Weight				0.3		g
F <sub>c</sub>	mounting force with clip		20		60	Ν

<sup>1)</sup> I<sub>BMS</sub> is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.





#### Part description

- D = Diode
- S = Schottky Diode A = Iow VF
- 15 = Current Rating [A]
- IM = Single Diode
- 200 = Reverse Voltage [V]
- UC = TO-252AA (DPak)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSA15IM200UC	SFMAUI	Tape & Reel	2500	510408

Similar Part	Package	Voltage class
DSB15IM30UC	TO-252AA (DPak)	30
DSA15IM45UC	TO-252AA (DPak)	45
DSA10IM100UC	TO-252AA (DPak)	100
DSA15IM150UC	TO-252AA (DPak)	150

Equiva	lent Circuits for	Simulation	* on die level	$T_{VJ} = 175 ^{\circ}C$
	- R <sub>o</sub> -	Schottky		
V <sub>0 max</sub>	threshold voltage	0.53		V
$\mathbf{R}_{0 \max}$	slope resistance *	7.6		mΩ

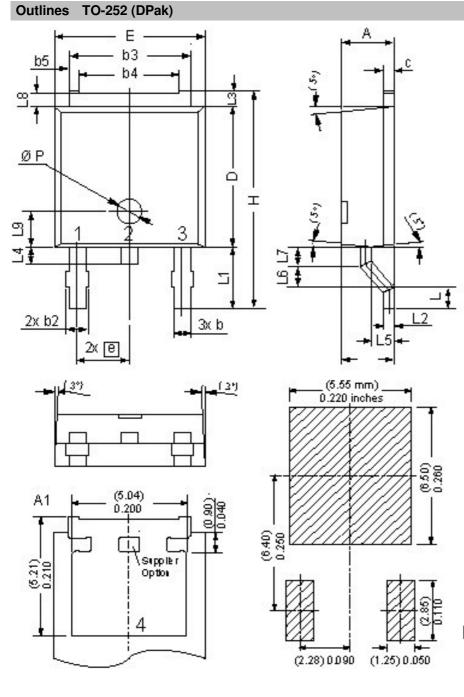
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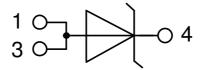
### DSA15IM200UC

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Dim.	Millimeters		Inches		
	min	max	min	max	
A	2.20	2.40	0.087	0.094	
A1	2.10	2.50	0.083	0.098	
b	0.66	0.86	0.026	0.034	
b2	10	0.96	i.	0.038	
b3	5.04	5.64	0.198	0.222	
b4	4.34	BSC	0.171	BSC	
b5	0.50	BSC	0.020	BSC	
С	0.40	0.86	0.016	0.034	
D	5.90	6.30	0.232	0.248	
Е	6.40	6.80	0.252	0.268	
е	2.10	2.50	0.083	0.098	
Н	9.20	10.10	0.362	0.398	
L	0.55	1.28	0.022	0.050	
L1	2.50	2.90	0.098	0.114	
L2	0.40	0.60	0.016	0.024	
L3	0.50	0.90	0.020	0.035	
L4	0.60	1.00	0.024	0.039	
L5	0.82	1.22	0.032	0.048	
L6	0.79	0.99	0.031	0.039	
L7	0.81	1.01	0.032	0.040	
L8	0.40	0.80	0.016	0.031	
L9	1.50	BSC	0.059	BSC	
ØΡ	1.00	BSC	0.039	BSC	

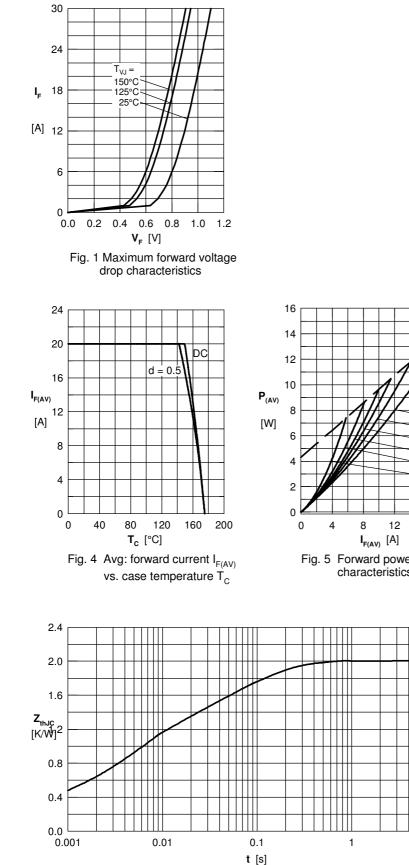
Recommended min. foot print

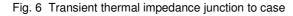


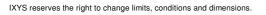
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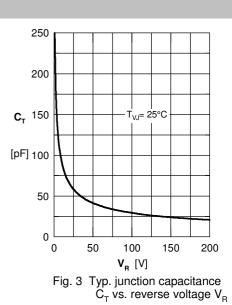
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### Schottky









d = DC 0.5 0.33 = 0.25 <sup>=</sup>0.17 •0.08 16 20 Fig. 5 Forward power loss characteristics

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